Crystalline $\beta$-Ga$_2$O$_3$ is a wide bandgap semiconductor (4.8-4.9 eV) which exhibits a high breakdown field of 8 MV/cm, high dielectric constant of 10 and electron mobility of >100 cm$^2$/V-s. This translates to a high voltage Baliga figure of merit (HV-FOM) that is more than 3000x that of Si, more than 8x that of 4H-SiC, and more than 4x that of GaN.

**Key Advantages**

- Potential for deep ultraviolet (UV) photodetectors and high speed & high power electronics

**Orientation:** (010) +/- 1°
**Conduction Type:** Semi-Insulating, Fe-doped
**Front Surface Finish:** Epi-ready, RMS < 0.5 nm
**Back Surface Finish:** Optical polish
**Edge Exclusion Area:** 1mm

**Available Sizes:** 25.4 mm +/- 1 mm
**Available Grades:** Prime
**Available Thickness:** 350 µm (± 50 µm)

*Other polishing options available: Double-side CMP, double-side optical*

*Other size, thickness and offcut options available*